

IN THE CLAIMS

Please delete claims 17-37 below.

1. (Original) A semiconductor device comprising:
 - a sealing body comprised of insulating region;
 - a metal-made support board which has at least a portion thereof covered with the sealing body and has a lower surface thereof exposed from the sealing body and constituting a first electrode;
 - a first electrode lead contiguous to the support board and projects from a one-side surface of the sealing body;
 - a second electrode lead and a control electrode lead which project from the one-side surface of the sealing body and extend parallel to the first electrode lead;
 - a semiconductor chip which is covered with the sealing body, has a first electrode on a lower surface thereof, has a second electrode pad and a control electrode pad on an upper surface thereof, and has a lower surface thereof fixed to the support board by a conductive bonding material;
 - connecting means which is positioned in the inside of the sealing body and electrically connects the second electrode pad with the second electrode lead; and
 - connecting means which is positioned in the inside of the sealing body and electrically connects the control electrode pad with the control electrode lead,
 - wherein the control electrode pad is arranged at a position from the control electrode lead and the second electrode lead farther than the second electrode pad.
2. (Original) A semiconductor device according to claim 1, wherein the semiconductor chip has a quadrangular shape, one side of the semiconductor chip opposingly faces lead posts formed to distal ends of the control electrode lead and the second electrode lead, and the control electrode pad is positioned at one corner portion of the semiconductor chip which is formed contiguously to a side of the semiconductor chip which is opposite to the opposingly facing side.
3. (Original) A semiconductor device according to claim 1, wherein the semiconductor chip has a quadrangular shape, one side of the semiconductor chip opposingly faces lead posts formed to distal ends of the control electrode lead and the second electrode lead, and the control electrode pad is positioned at a midst portion of a side which is

formed contiguously to the opposingly facing side and is orthogonal to the opposingly facing side.

4. (Original) A semiconductor device according to claim 1, wherein the connecting means is formed of a conductive wire, the second electrode pad and the second electrode lead are connected with each other through a plurality of wires, and the wires are thicker than a wire which connects the control electrode pad and the control electrode lead.
5. (Original) A semiconductor device according to claim 1, wherein a width of the second electrode lead is set wider than a width of other leads.
6. (Original) A semiconductor device according to claim 1, wherein the first electrode lead is positioned at the center, the control electrode lead is positioned at one side of the first electrode lead, and the second electrode lead is positioned at another side of the first electrode lead.
7. (Original) A semiconductor device according to claim 1, wherein the second electrode lead is positioned at the center, the control electrode lead is positioned at one side of the second electrode lead, and the first electrode lead is positioned at another side of the second electrode lead.
8. (Original) A semiconductor device according to claim 1, wherein a plurality of second electrode pads are provided and the respective second electrode pads and the second electrode lead are electrically connected with each other by the connecting means.
9. (Original) A semiconductor device according to claim 8, wherein the plurality of second electrode pads are formed along the extending direction of the respective leads and the connecting means which is connected to the second electrode leads adopts the stitch bonding constitution in which the connecting means is connected with the plurality of second electrode pads respectively.

10. (Original) A semiconductor device according to claim 8, wherein the plurality of second electrode pads are formed in a staggered pattern along the direction which intersects the extending direction of the respective leads.
11. (Original) A semiconductor device according to claim 1,
wherein the connecting means which connects the second electrode pad with the second electrode lead is formed of a conductive plate, and the connecting means which connects the control electrode pad with the control electrode lead is formed of a wire.
12. (Original) A semiconductor device according to claim 11, wherein the conductive plate is formed of a resilient ribbon strap and is connected with the second electrode pad and the second electrode lead by ultrasonic wave bonding connection.
13. (Original) A semiconductor device according to claim 11, wherein the conductive plate is formed of a metal plate molded in a predetermined shape and is connected with the second electrode pad and the second electrode lead by an adhesive material.
14. (Original) A semiconductor device according to claim 1,
wherein with respect to the leads which project from the sealing body, the second electrode lead and the control electrode lead have the surface mounting structure in which the second electrode lead and the control electrode lead have mid portions thereof bent and distal ends thereof extended while being positioned at a height equal to a height of the support board, and
wherein the first electrode lead which is formed contiguously with the support board is formed of a lead which is cut in the vicinity of the sealing body and is not used, or adopts the surface mounting structure having the same constitution as the second electrode lead and the control electrode lead.
15. (Original) A semiconductor device according to claim 1, wherein the semiconductor chip includes any one of transistors comprised of a power MOSFET, a power bipolar transistor and IGBT which respectively use the first electrode, the second electrode and the third electrode as electrodes.

16. (Original) A semiconductor device according to claim 1, wherein a field effect transistor is incorporated into the semiconductor chip, the first electrode lead constitutes a drain lead, the control electrode lead constitutes a gate lead, and the second electrode lead constitutes a source lead.

17-37 (Canceled)